

C2 78. (Amended) The method of claim 76 wherein exposing the wafer to a material selected from the group consisting of phosphine and boron trichloride comprises exposing the wafer to this selection prior to exposing the wafer in situ to a reducing environment.

79. (Amended) The method of claim 76 wherein exposing the wafer to a material selected from the group consisting of phosphine HCL, and boron trichloride comprises exposing the wafer to this selection prior to depositing the second conductive layer.

Please add new claims 80-92 as follows:

C3 Sub DI --80. (New) The method of claim 76 wherein the first conductive layer comprises hemispherical silicon grain and wherein the second conductive layer comprises tungsten nitride.

81. (New) The method of claim 76 wherein the first conductive layer comprises tungsten nitride and wherein the second conductive layer comprises polysilicon.

82. (New) The method of claim 76 further comprising forming a third conductive layer on the second conductive layer.

<sup>3</sup> 83. (New) The method of claim <sup>2</sup> 82 further comprising forming a borophosphosilicate glass layer on the third conductive layer.

<sup>4</sup> 84. (New) The method of claim <sup>3</sup> 83 wherein the first conductive layer comprises hemispherical silicon grain, the second conductive layer comprises tungsten nitride, and the third conductive layer comprises polysilicon.

85. (New) A method of treating a wafer, comprising:  
depositing a first conductive layer onto the wafer;  
exposing the wafer to a reducing environment;

depositing a second conductive layer; and  
 passivating at least one of the first and second conductive layers by  
 exposing the wafer to a material selected from the group consisting of diborane, phosphine,  
 HCL, and boron trichloride.

86. (New) The method of claim 85 wherein passivating at least one of the first  
 and second conductive layers comprises exposing the wafer to the recited group prior to  
 exposing the wafer in situ to a reducing environment.

87. (New) The method of claim 85 wherein passivating at least one of the first  
 and second conductive layers comprises exposing the wafer to the recited group prior to  
 depositing the second conductive layer.

Sub D2  
 88. (New) The method of claim 85 wherein the first conductive layer  
 comprises hemispherical silicon grain and wherein the second conductive layer comprises  
 tungsten nitride.

89. (New) The method of claim 85 wherein the first conductive layer  
 comprises tungsten nitride and wherein the second conductive layer comprises polysilicon.

90. (New) The method of claim 85 further comprising forming a third  
 conductive layer on the second conductive layer.

<sup>17</sup>/<sub>91</sub>. (New) The method of claim <sup>16</sup>/<sub>90</sub> further comprising forming a  
 borophosphosilicate glass layer on the third conductive layer.

<sup>18</sup>/<sub>92</sub>. (New) The method of claim <sup>17</sup>/<sub>91</sub> wherein the first conductive layer  
 comprises hemispherical silicon grain, the second conductive layer comprises tungsten nitride,  
 and the third conductive layer comprises polysilicon.--